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[54] **SOLID-STATE IMAGE SENSING APPARATUS AND MANUFACTURING METHOD THEREOF**

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[52] **U.S. Cl.** ..... **257/680**; 257/686; 257/688; 257/689; 257/724; 257/725

[58] **Field of Search** ..... 257/680, 686, 257/688, 689, 700, 724, 725

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[57] **ABSTRACT**

A lead frame **24** comprising an inner lead **22** and outer lead **23** is sealingly filled from a through-hole into a package **21**. A CCD chip **27** is inserted from an inlet **26** into the package **21**. An electrode pad **28** is connected to the inner lead **22** via a bump **29** to complete an optical positioning and an electrical connection, then the positions of these components are fixed by glue. As a result, a solid-state image sensing apparatus can be manufactured at a low cost, and an accurate positioning can be realized. Thus, the solid-state image sensing apparatus can be employed to a video camera of high quality picture to reproduce vivid colors and fine pictures.

**16 Claims, 6 Drawing Sheets**

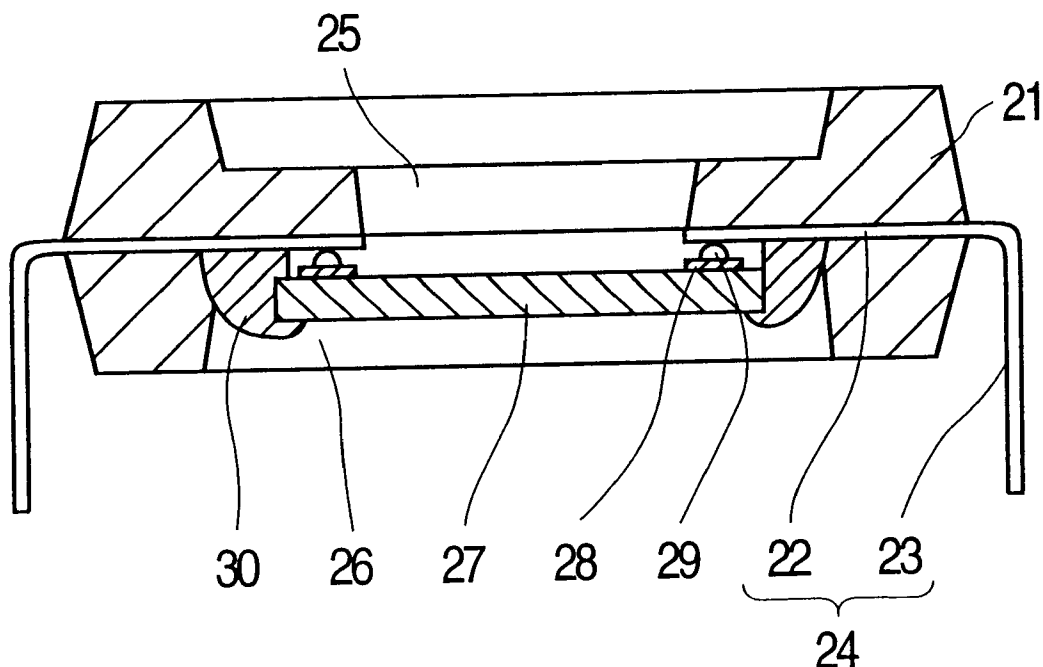


FIG. 1

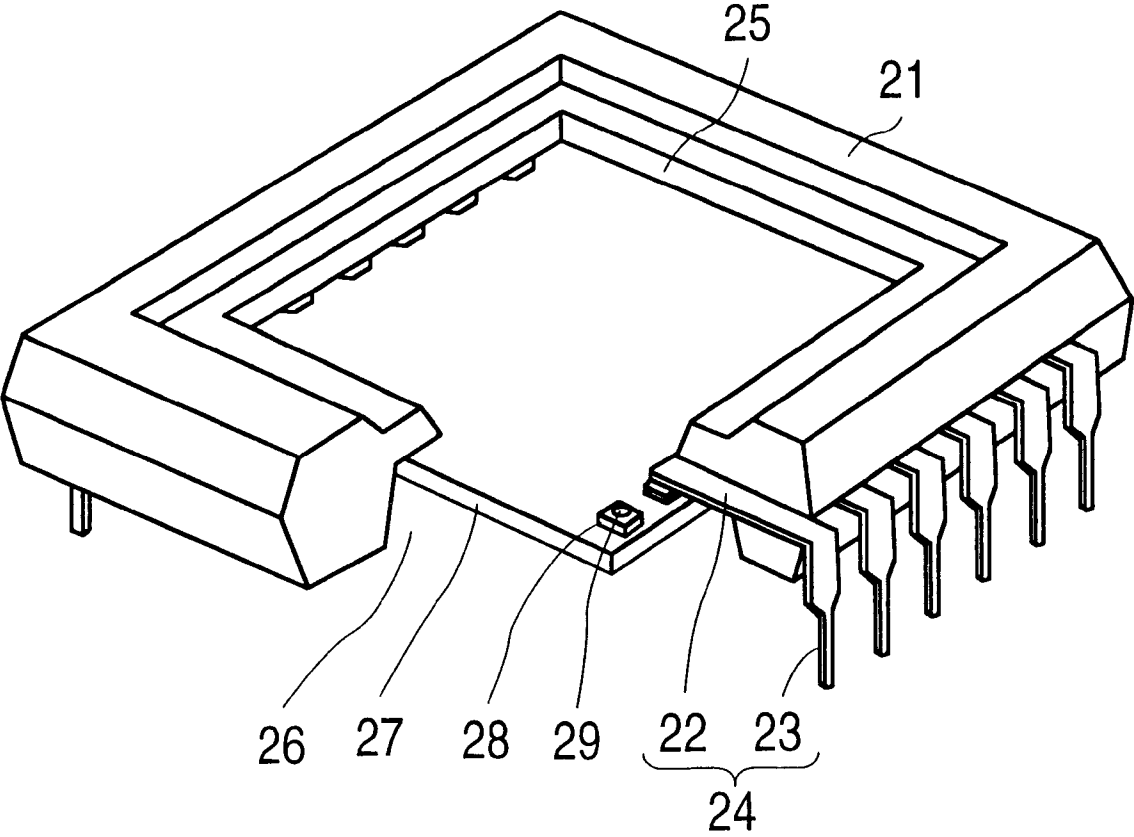


FIG. 2

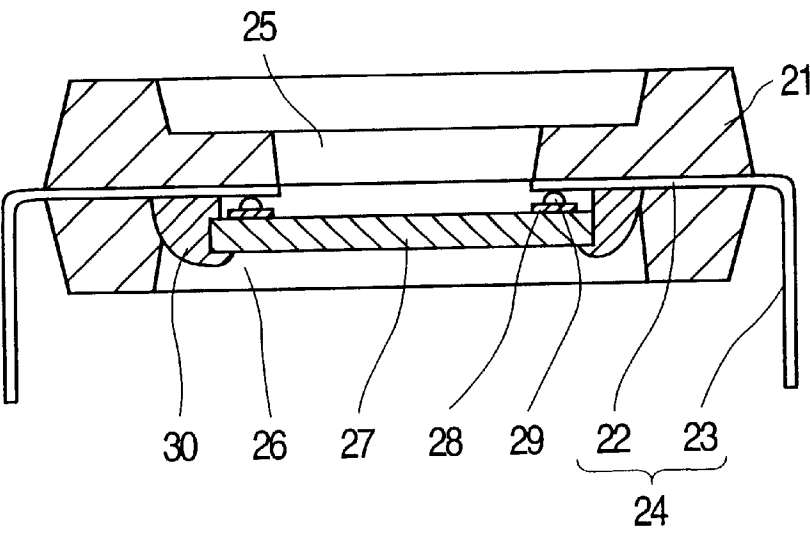


FIG. 3

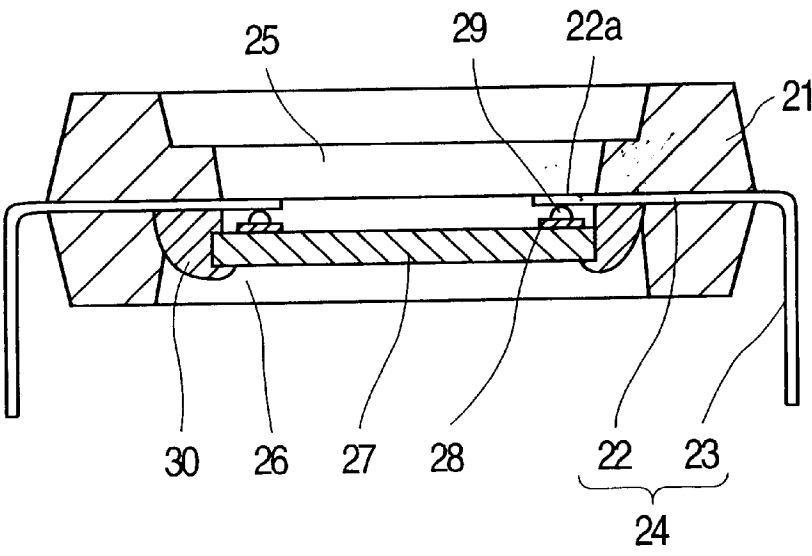


FIG. 4

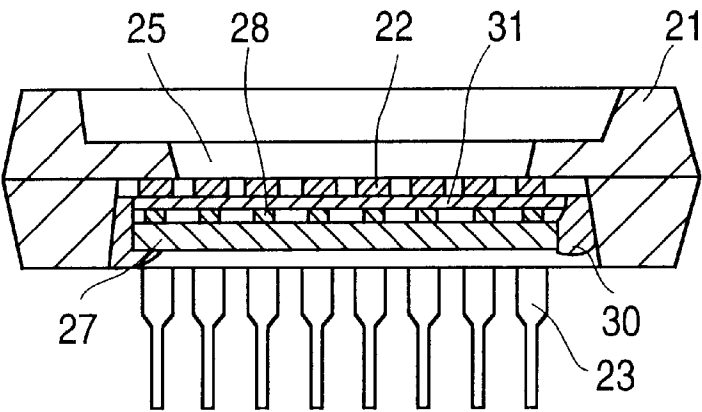


FIG. 5

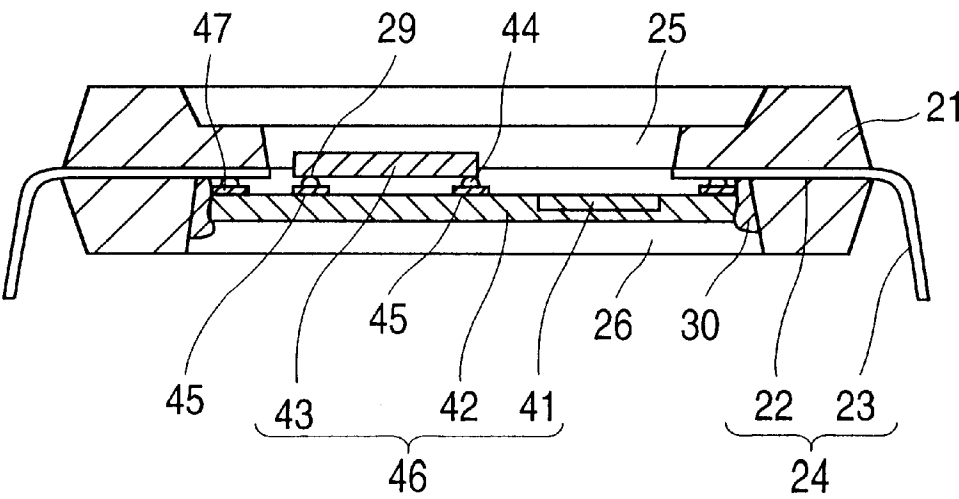


FIG. 6

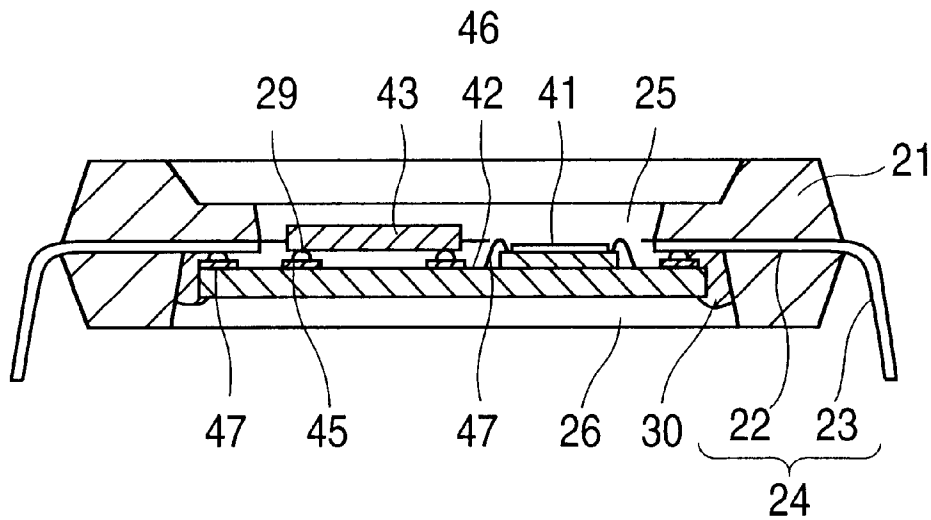


FIG. 7

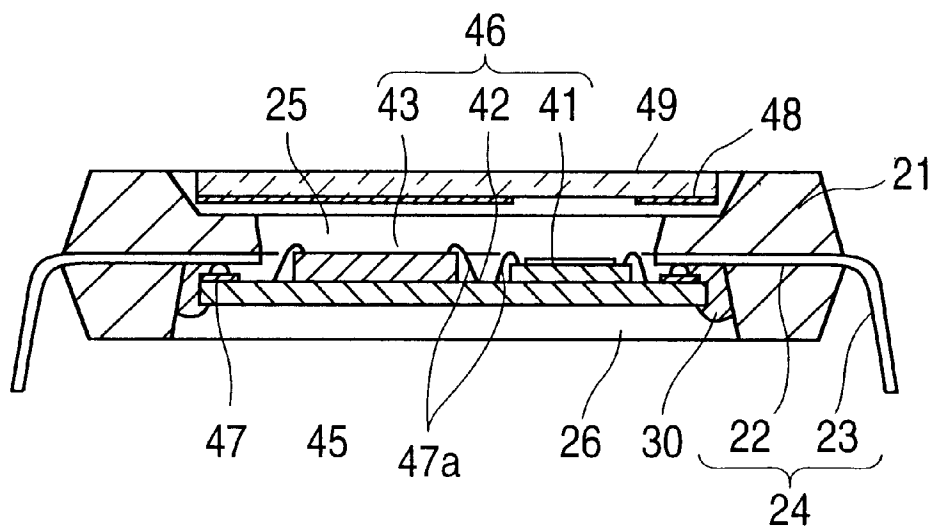
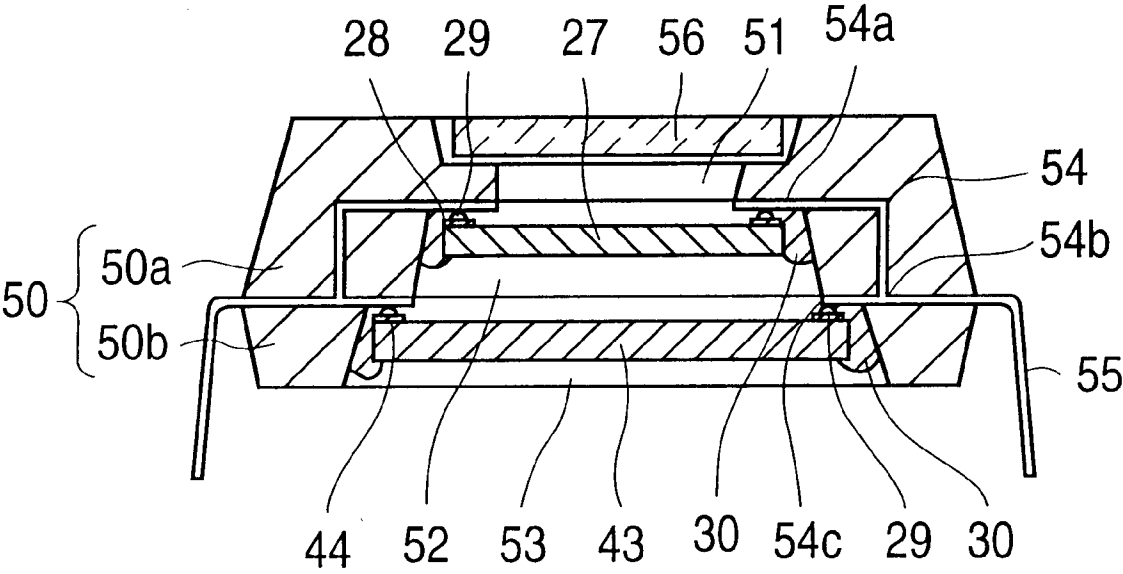
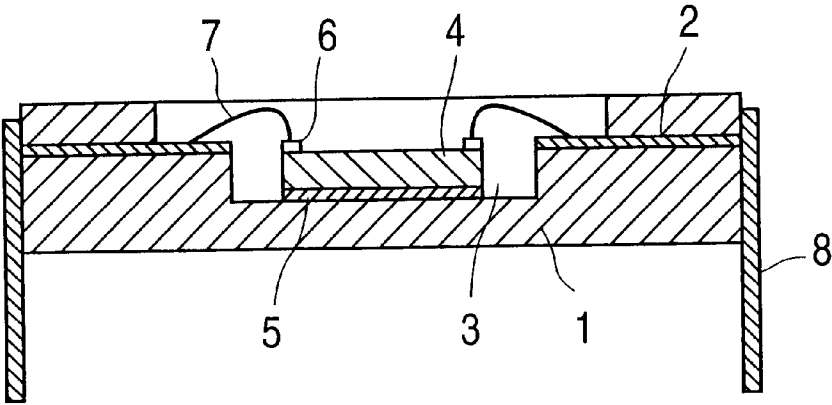


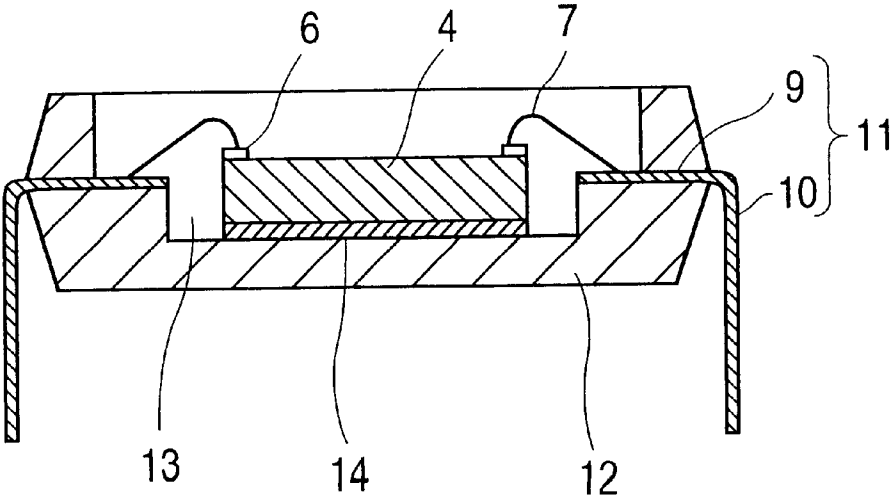
FIG. 8



**FIG. 9**  
*PRIOR ART*



**FIG. 10**  
*PRIOR ART*



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# SOLID-STATE IMAGE SENSING APPARATUS AND MANUFACTURING METHOD THEREOF

## FIELD OF ENGINEERING

The present invention relates to a solid-state image sensing apparatus using a solid-state image sensing device (hereinafter called CCD chip) in a package made of plastic, ceramic or glass(hereinafter called package), more particularly to a solid-state image sensing apparatus using three CCD chips, which is used for a video camera and required severe optical positioning accuracy. The present invention also relates to the manufacturing method of the solid-state image sensing apparatus.

## BACKGROUND OF ENGINEERING

Recently, a video camera, a home-use video camera among others, has been equipped with the better functions in addition to its reducing size and weight. Consumers have demanded the better quality picture such as of high color fidelity as well as displaying detail. In order to satisfy this demand, technical levels relating to many components of the video camera have been highly enhanced, and in particular, performance of the CCD chip which is called "a heart of video camera," has been remarkably progressed in increasing a number of pixels. On the other hand, a home-use video camera of which main stream has been one-eye video camera using one CCD chip, starts replacing the one-eye with a three-eye using three CCD chips which has been employed in an expensive professional video camera, namely, three CCD chips correspond to Red, Green, Blue colors. Comparing with the one-eye video camera, the three-eye video camera is required an ultra positioning accuracy because three CCD chips are to be optically disposed at correct positions. Since the home-use video camera has been designed to be portable and smaller in size, many of the components are mounted in an extreme high density. Therefore, the solid-state image sensing apparatus for the home-use video camera is required to change itself in its own structure.

FIG. 9 and FIG. 10 depict a conventional solid-state image sensing apparatus. FIG. 9 is a cross section of a solid-state image sensing apparatus in a ceramic package which was once a mainstream. A ceramic package 1, on which metallized conductor 2 is formed, has a concave part 3 in the center thereof. On the concave part 3, a CCD chip 4 is mounted by die bonding, and an electrode pad 6 of CCD chip 4 is wire-bonded to the metallized conductor 2 by a metal lead 7. A lead terminal 8 is deposited to an end face of metallized conductor 2 exposing itself from the side of ceramic package 1.

FIG. 10 is a cross section of a solid-state image sensing apparatus in a plastic package. A lead frame 11 comprising an inner lead 9 and an outer lead 10 is imolded in a plastic package 12. At a center of the plastic package, a concave portion 13 is situated. The CCD chip 4 is di-bonded by conductive paste 14 to the concave portion 13, and the electrode pad 6 on the CCD chip 4 is wire-bonded to the inner lead 9 by the metal lead 7 as same as the case of the ceramic package shown in FIG. 9.

However, according to the above conventional solid-state image sensing apparatus and the manufacturing method thereof, the CCD chip in either the ceramic package 1 or plastic package 12, is mounted on the base of either concave part 3 or 13 by die bonding. When this conventional solid-state image sensing apparatus having the above struc-

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ture is mounted to the three-eye video camera and is accurately positioned in optical manner, the base of concave part 3 or 13 of ceramic package 1 or plastic package 12 to which the CCD chip 4 is die-bonded should be processed in high accuracy. Also a level of parallelism with regard to the base and an upper face of ceramic package 1 or plastic package 12 should be highly accurate. These factors not only increase a cost of ceramic package 1 or plastic package 12 but also raise a cost of mounting process of CCD chip 4. The wire-bonding method for connecting the electrode pad 6 of CCD chip 4 with the metallized conductor 2 or the inner lead 9 via the metal lead 7 is a classic manufacturing technique expecting a low defect ratio and requiring little effort for replacing chips; however, this method limits the size reduction of solid-state image sensing apparatus, and cannot fully respond to a request of reducing a size thereof from the market of home-use video camera.

## DISCLOSURE OF THE INVENTION

The present invention aims to provide a solid-state image sensing apparatus mountable to a video camera of high quality picture, which not only can reproduce vivid colors and fine pictures but also can be manufactured at a low cost. The present invention also aims to provide a manufacturing method of the solid-state image sensing apparatus.

The solid-state image sensing apparatus according to the present invention comprises a package having a through hole therein, a lead frame comprising an inner lead and an outer lead sealed therein, and a CCD chip loaded therein. Both the end faces of the package have different opening areas. The CCD chip can be mounted from the opening having the wider opening area, and thereby shutting the through hole tightly.

Another type of the solid-state image sensing apparatus according to the present invention has the opening of the package. The electrode pad of CCD chip is connected via the inner lead to the opening, and the opening area is smaller than the entire area of CCD chip.

Still another type of the solid-state image sensing apparatus according to the present invention has the package having a through hole therein, and the lead frame comprising the inner lead and outer lead sealed therein, and a substrate on which the CCD chip and peripheral circuit elements are mounted being loaded into the package from the opening which has the wider opening area, and the electrode pad of substrate connected to the inner lead exposed from a periphery of end face of the opening which has the smaller opening area.

Further another type of the solid-state image sensing apparatus of the present invention has the package having a through hole therein, and the lead frame comprising the inner lead and outer lead sealed therein, and the peripheral circuit elements mounted on a substrate which is disposed on an upper surface of the substrate excluding the surface where the CCD chip is mounted. The two substrates are loaded into the package from the opening which has the wider opening area. The electrode pad is connected to the inner lead exposed from the periphery end face of the opening which has the smaller opening area.

Another type of the solid-state image sensing apparatus of the present invention has the package having the through hole therein, and the lead frame comprising the inner lead and outer lead sealed therein, and the CCD chip fixed and coupled to a first inner lead exposed from a first step of the package, and the peripheral circuit elements fixed and connected to a second inner lead exposed from a second step of the package.



A manufacturing method according to the present invention relates to the solid-state image sensing apparatus which has the package comprising a through hole therein, and the lead frame comprising the inner lead and outer lead sealed therein, and the CCD chip mounted therein. The CCD chip is loaded into the through hole of the package from the opening which has the wider opening area. The electrode pad of solid-state image sensing apparatus is coupled to the inner lead via a bump or an anisotropic conductor having only vertical conductivity so that optical positioning as well as electrical connecting is completed. Then a back side of the CCD chip is glued to the package by adhesive.

Another manufacturing method according to the present invention relates to the solid-state image sensing apparatus which has the package comprising the through hole therein, and the lead frame comprising the inner lead and outer lead sealed therein, and the CCD chip as well as the peripheral circuit elements mounted therein. The CCD chip and group of wirings are formed on a semi-conductor substrate, then the periphery circuit elements are disposed on the substrate excluding a preoccupied place by the CCD chip, and connected to the group of wirings. Next, the substrate is loaded into the through hole from the opening which has the wider opening area. The electrode pad disposed around the upper surface of the substrate is connected to the inner lead via the bump or anisotropic conductor so that the optical positioning as well as electrical connection is completed. Then the back side of the substrate having the CCD chip and peripheral circuit elements thereon is glued to the package by adhesive.

Still another manufacturing method according to the present invention relates to the solid-state image sensing apparatus which has the package comprising the through hole therein, and the lead frame comprising the inner lead and outer lead sealingly filled therein, and the CCD chip as well as the peripheral circuit elements loaded therein. The CCD chip and the peripheral circuit elements are mounted on the substrate where the group of wirings were already disposed, and the CCD chip and the peripheral circuit elements are connected to the group of wirings. The substrate is loaded into the through hole from the opening which has the wider opening area. The electrode pad disposed at periphery of the upper surface of the substrate is connected to the inner lead via the bump or anisotropic conductor so that the optical positioning as well as electrical connection is completed. Then the back side of the substrate having the CCD chip and peripheral circuit elements thereon is glued to the package by adhesive.

Further another manufacturing method according to the present invention relates to the solid-state image sensing apparatus which has the package comprising the through hole therein, and the lead frame comprising the inner and outer leads sealed therein, and the CCD chip as well as the peripheral circuit elements mounted therein. The CCD chip is loaded into the through hole of the package from the opening which has the wider opening area, and the electrode pad is connected to the first inner lead via the bump or the anisotropic conductor so that optical positioning as well as electrical connection is completed. Then the back side of the CCD chip is glued to the package by adhesive, and the peripheral circuit elements is loaded into the through hole from the same opening used when the CCD chip loaded. The electrode pad of the peripheral circuit elements is electrically connected to the second inner lead via the bump or the anisotropic conductor, and then the back side of the peripheral circuit elements is glued to the package by adhesive.

According to the present invention, the through hole is provided in the package, and the CCD chip can be loaded

into the package from the bottom side, namely from the opening which has the wider opening area. The electrode pad of CCD chip is electrically connected to the bump or the anisotropic conductor, and also optically positioned at the same time. Thus, the present invention can reduce a number of manufacturing processes comparing with the conventional method which requires two bonding processes including the die-bonding of CCD chip and the wire-bonding of electrode pad. Further, because a loading jig for the CCD chip can be disposed at the back side of CCD chip, the CCD chip can be optically positioned with ease from the front, thus more accurate positioning can be expected.

#### BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a cutaway perspective view of the solid-state image sensing apparatus of an exemplary embodiment of the present invention.

FIG. 2 is a cross section of the solid-state image sensing apparatus of the first exemplary embodiment of the present invention.

FIG. 3 is a cross section of the solid-state image sensing apparatus of the second exemplary embodiment of the present invention.

FIG. 4 is a cross section of the solid-state image sensing apparatus of the third exemplary embodiment of the present invention.

FIG. 5 is a cross section of the solid-state image sensing apparatus of the fourth exemplary embodiment of the present invention.

FIG. 6 is a cross section of the solid-state image sensing apparatus of the exemplary embodiment of the present invention.

FIG. 7 is a cross section of the solid-state image sensing apparatus of the sixth exemplary embodiment of the present invention.

FIG. 8 is a cross section of the solid-state image sensing apparatus of the seventh exemplary embodiment of the present invention.

FIG. 9 is a cross section of a conventional solid-state image sensing apparatus.

FIG. 10 is a cross section of another conventional solid-state image sensing apparatus.

#### THE DESCRIPTION OF PREFERRED EMBODIMENT

An exemplary embodiment of the present invention is stated here by referring to FIG. 1, which is a cutaway perspective view of an exemplary embodiment according to the present invention. A lead frame 24 comprising an inner lead 22 and an outer lead 23 is inmolded in a package 21. As FIG. 1 depicts, a through hole is provided at the center of the package 21, and in front side of the package 21, an opening 25 which has a smaller opening area is situated, and another opening 26 (hereinafter called "inlet" which has a wider opening area is situated at the back side thereof. The area of opening 25 is smaller than that of CCD chip 27. An inner lead 22 is exposed from the back side of a step between the opening 25 and the inlet 26, and the inner lead 22 is electrically connected to a bump 29 disposed on an electrode 28 of CCD chip 27.

Next, a manufacturing method according to the present invention is described. FIG. 2 is a cross section of the solid-state image sensing apparatus according to the first exemplary embodiment of the present invention. Epoxy

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resin mixed with inorganic filler is injected into a mold where the lead frame **24** made of phosphor bronze, etc. is disposed, and is inmolded at a high temperature. Then the package **21** is taken out from the mold. A frame body of the lead frame **24** is cut away, and the outer lead **23** is bent toward the inlet **26**, thereby forming the package **21**. The bump **29** is formed on the electrode pad **28** of the CCD chip **27**, whose back side is held by a mounting jig(not shown), and the CCD chip **27** is inserted into the package **21** from the net **26**. Then, the bump **29** is press-fitted and connected to the inner lead **22** which is exposed from a back side of the step situated between the opening **25** and the net **26**. During this press-fit operation, a position signal is feed-backed from a optical position adjusting device(not shown) disposed in front of the CCD chip **27** to the mounting jig, thereby finely adjusting an orientation of the CCD chip **27** and disposing the CCD chip **27** on the back side of the step of the package **21**. At the same time, ultra-violet hardening adhesive **30** is injected in a specified quantity from a dispenser which is situated beside a press-fit jig to glue four sides of the CCD chip **27** to the package **21**, and finally, the CCD chip **27** is accurately mounted to the package **21**.

FIG. **3** is a cross section of the solid-state image sensing apparatus used in a second exemplary embodiment of the present invention. A different point from the first exemplary embodiment is this: a tip **22a** of the inner lead **22** slightly protrudes from the opening **25** toward inside. This structure facilitates the optical positioning as well as the bonding between the inner lead and the bump **29** thanks to elasticity of the tip **22a**.

In the first and second exemplary embodiments, the bump **29** is disposed on the electrode pad **28**; however, the bump **29** may be disposed at the tip of inner lead **22** and coupled with the electrode pad **28** of CCD chip **27**.

FIG. **4** is a cross section of the solid-state image sensing apparatus used in Embodiment 3. The inner leads **22** are cut so that they seem to be arranged in parallel from their cross sectional view. In this embodiment, the electrode pad **28** of CCD chip **27** and the inner leads **22** are connected via the anisotropic conductor **31** which has conductivity in only the vertical direction instead of via the bump **29**. Thanks to the elasticity of anisotropic conductor **31** made of conductive rubber or the like, the CCD chip **27** can be optically positioned with ease as same as the second embodiment.

According to this exemplary embodiment, an assembly process can be substantially simplified because of the structure as follows: the through hole is provided in the package **21**, and the CCD chip **27** is loaded from the inlet **26** which is situated on the back side of package **21**, namely, on the side of outer leads, and the exposed inner lead **22** from the back side of the step situated between the opening **25** and the inlet **26** is connected to the electrode pad **28** of CCD chip **27** electrically via the bump or anisotropic conductor, at the same time, an optical positioning between the inner lead **22** and the electrode pad **28** is completed. Further, since the mounting jig of CCD chip **27** can be disposed on the back side of CCD chip **27**, the CCD chip **27** can be optically positioned from the front with ease, thus an accurate positioning can be achieved.

FIG. **5** is a cross section of the solid-state image sensing apparatus used in Embodiment 4. Epoxy resin mixed with inorganic filler is injected into a mold where the lead frame **24** made of phosphor bronze, etc. are disposed, and is inmolded at a high temperature. Then the package **21** is taken out from the mold. A frame body of the lead frame **24** is cut away, and the outer lead **23** is bent toward the inlet **26**,

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thereby forming the package **21**. A substrate **42** comprising a semiconductor substrate such as silicon wafer, on which a group of wirings (not shown) and a CCD chip **41** are formed, and on a part of the substrate surface, a peripheral circuit elements **43** are disposed in a face-down way; the peripheral circuit elements **43** were produced in a separate manufacturing process. A bump **29** disposed on an electrode pad **44** of the peripheral circuit elements is connected to an electrode pad **45** of the group of wirings on the substrate **42**, thereby producing a function device **46** (hereinafter called "CCD module"). A back side of the CCD module **46** is held by a mounting jig (not shown), and is inserted from the inlet **26** into the package **21**. Then, the bump **29** on an electrode pad **47** disposed around the CCD module **46** is press-fitted to the inner lead **22** exposed from the back side of the step situated between the opening **25** and the inlet **26**, thus the bump **29** is electrically connected with the inner lead **22**. During this press-fit operation, a position signal is feed-backed from an optical position adjusting device(not shown) disposed in front of the CCD chip **41** to the mounting jig, thereby finely adjusting an orientation of the CCD chip **41** and disposing the CCD module **46** on the back side of the step of the package **21**. At the same time, ultra-violet hardening adhesive **30** is injected in a specified quantity from a dispenser which is situated beside a press-fit jig to glue four sides of the CCD chip **41** to the package **21**, and finally, the CCD chip **41** is accurately mounted to the package **21**.

FIG. **6** is a cross section of the solid-state image sensing apparatus used in Embodiment 5 of the present invention. This embodiment is one of variations of Embodiment 4 described above. The method of accurately mounting the CCD chip **41** to the package **21** is the same as that of the Embodiment 4 from the standpoints of structure and manufacturing, namely, the CCD module **46** on which the CCD chip, peripheral circuit elements and the group of wirings are formed, is inserted from the inlet **26**, and the CCD module **46** is fixed to the package **21**, while the optical position of CCD chip **41** is fine adjusted. A different point from the Embodiment 4 is this: in Embodiment 4, the CCD chip is formed directly on the semiconductor substrate, which is to be the substrate **42** of the CCD module **46**, through a circuit-chip-forming-process such as a direct diffusion process, on the other hand in Embodiment 5, the CCD chip **41** as well as peripheral circuit elements **43** was already produced in a separate process, and the CCD chip **41** and peripheral circuit elements **43** are disposed on the substrate **42** on which the group of wirings have been formed, and thereby they are electrically connected to form the CCD module **46**.

Accordingly, the substrate **42** used in this embodiment may be made of a material other than semiconductor. As shown in FIG. **6**, when the CCD chip **41** produced in the separate process is mounted on the substrate **42**, the electrode of CCD chip **41** is wire-bonded to the electrode terminal of the group of wirings by using a metal wire **47a**.

FIG. **7** is a cross section of the solid-state image sensing apparatus used in Embodiment 6. This embodiment is also one of variations of Embodiment 5 above mentioned. A different point from Embodiment 5 is this: in Embodiment 5, the peripheral circuit elements **43** are connected to the substrate **42** via the bump **29** in the face-down way same as that in Embodiment 4; however, in this Embodiment 6, the peripheral circuit elements **43** are disposed on the substrate **42** in the face-up way(the face on which a circuit is formed is situated upward) as the CCD chip **41** is in Embodiment 5, and the electrode of peripheral circuit elements is wire-

bonded to the electrode terminal of the group of wiring by using the metal wire **47a**.

Embodiments 4, 5, and 6 have some similarities as well as differences with each other. An advantage of the solid-state image sensing apparatus in these embodiments are as follows.

First, in Embodiment 4, since the CCD chip **41** is formed on the substrate **42** together with other groups of wirings at the same time, the electrode of CCD chip **41** is electrically connected to the electrode terminals of the groups of wirings with ease and reliably. Therefore, Embodiment 4 is effective for reducing the size of the solid-state image sensing apparatus.

Second, in Embodiment 5, since the CCD chip, which has a large number of pixels to be highly accurate and, as a result, an yield ratio generally has to be extraordinarily low, is produced in the separate process, only defect-free CCD chips are put into the assembly process, thereby reducing the total cost.

Third, in Embodiment 6, the electrodes of CCD chip **41** and peripheral circuit elements **43** are connected to the electrode terminal of group of wirings by mounting technique or wire-bonding method, both are classic techniques and have high reliability based on ample experience of mounting engineering and automatic mounting machines. Since the surface on which the circuit elements **43** are formed is situated upward, a shading film **48** is required; however, when defects are found in the CCD chip **41** or the peripheral circuit elements **43**, the defective parts can be easily replaced and the other parts also can be used again. In FIG. 7, a glass substrate **49** is made from the shading film by being deposited with metal or by sputtering.

As described above, the solid-state image sensing apparatus in Embodiments 4, 5, or 6 is used depending on a requested performance, price, and application.

FIG. 8 is a cross section of the solid-state image sensing apparatus used in Embodiment 7. A different point from the above embodiments is this: the CCD chip and peripheral circuit elements are mounted in multilayered structure situated in the package, therefore, the package structure of this embodiment is different from those of the above embodiments, namely, the CCD chip and peripheral circuit elements are inserted into the package from the through hole comprising two openings both having wide and different opening areas.

A structure and manufacturing method of Embodiment 7 is described as follows. In FIG. 8, a package **50** having an original structure is employed in Embodiment 7. A first opening **51** having a small opening area is disposed on a first end face, a second opening **52** having a large opening area and a third opening **53** having the larger opening area than that of the opening **52** are disposed on a second end face. Regarding a package **50**, its upper frame **50a** has the first opening **51** and the second opening **52**, and also has a bent inner lead **54** situated therein. A first end of the inner lead **54** forms an exposed terminal **54a** of the inner lead from a step situated between the first opening **51** and second opening **52**. A second terminal **54b** of inner lead **54** bent and extended downward from inside of the upper frame **50a** is sealed between a lower frame **50b** and the upper frame **50a**, and the end of the terminal **54b** is connected in the package to a junction point of an inner lead terminal **54c** exposed from a step between the second opening **52** and third opening **53** with an outer lead **55** which is bent outside of the package **50**.

The manufacturing method shown in FIG. 8 is, first, as same as the Embodiment 1, the epoxy resin mixed with

inorganic filler is injected into a mold where the lead frame comprising the inner lead **54** made of phosphor bronze, etc. and the outer lead **55** is disposed, and is inmolded at a high temperature. Then the package **50** is taken out from the mold. A frame body of the lead frame is cut away, and the outer lead **55** is bent toward the inlet **26**, thereby forming the package **50**. The bump **29** is formed on the electrode pad **28** of the CCD chip **27**, whose back side is held by a mounting jig(not shown), and the CCD chip **27** is inserted into the package **50**. Then, the bump **29** is press-fitted and connected to the inner lead terminal **54a** which is disposed at a first step situated on the upper frame of the package **50**. During this press-fit operation, a position signal is feed backed from an optical position adjusting device(not shown) disposed in front of the CCD chip **27** to the mounting jig, thereby an orientation of the CCD chip **27** is finely adjusted and the CCD chip **27** is positioned at the back side of the step of the package **50**. At the same time, ultra-violet hardening adhesive **30** is injected in a specified quantity from a dispenser which is situated beside a press-fit jig to glue four sides of the CCD chip **27** to the package **50**, and finally, the CCD chip **27** is accurately mounted to the package **50**.

Then, the peripheral circuit elements **43** are also inserted into the lower frame **50b** of package **50** from the third opening **53**, and the electrode pad **44** of peripheral circuit elements **43** are connected via the bump **29** by press-fit to the second inner lead terminal **54c** which is exposed from the step between the second opening **52** and third opening **53**. At the same time, ultra-violet hardening adhesive **30** is injected in a specified quantity from a dispenser which is situated beside a press-fit jig to glue four sides of the peripheral circuit elements **43** to the package **50**, and finally, the peripheral circuit elements **43** are accurately mounted to the package **50**.

Thus, according to Embodiment 7, the CCD chip **27** and peripheral circuit elements **43** are disposed in multilayered or vertical structure within the package **50**, and the driving circuit can be incorporated into the solid-state image sensing apparatus, thereby reducing an area occupied by parts mounted on the substrate. As a result, a high density mounting into a small size video camera can be realized.

A protection panel **56**, made of transparent material such as glass, is shown in FIG. 8. The protection panel **56** protects the inside of solid-state image sensing apparatus; however, whether using of this protection panel **56** or not does not change the functions as well as effects of the present invention described in the above embodiments.

In Embodiment 5 through Embodiment 7, the tip of inner lead can be slightly protruded from the opening toward inside of package, as described in Embodiment 3. Thus, the optical positioning and bonding with the bump can be completed with ease thanks to the elasticity of the inner lead tip. Further, in the above Embodiments 1 and 2, the case is described that the bump **29** is disposed on the electrode pad **28** of CCD chip **27**; however, the bump **29** can be disposed at the tip of inner lead **22** and connected with the electrode pad **47** of CCD module **46**.

In Embodiment 5 through Embodiment 7, the electrode pad **47** of CCD module **46** can be connected to the inner lead terminal via, instead of the bump **29**, the anisotropic conductor which has only vertical conductivity, as described in Embodiment 4.

#### Industrial Applicability

According to the above solid-state image sensing apparatus and the manufacturing method thereof of the present

invention, the invention relates to the solid-state image sensing apparatus comprising a through hole therein, the lead frame comprising the inner and outer leads which are sealed in the package, and the CCD chip as well as peripheral circuit elements mounted in the package, and also relates to the manufacturing method of the same. The package has the openings on both end faces, and the areas of the openings differ with each other. The CCD chip is inserted from the larger opening into the package, thereby sealing the through hole. Since the electrode pads of CCD chip and that of the peripheral circuit elements are connected to the inner leads via the anisotropic conductor, a number of manufacturing processes can be greatly reduced. Further, the mounting jig of CCD chip is disposed behind the CCD chip and the CCD chip is optically positioned from the front, thus highly accurate positioning can be achieved. As a result, the solid-state image sensing apparatus, which enables a video camera to reproduce vivid colors as well as fine pictures, can be manufactured at a low cost.

What is claimed is:

1. A solid-state image sensing apparatus comprising:
  - a package having a through hole therein, openings on both end faces thereof, and different opening areas of said openings,
  - a lead frame comprising inner leads and outer leads, said lead frame being sealed in said package, and
  - a solid-state image sensing device mounted in said package by being inserted from an inlet of said opening which has a wider area, and thereby sealing said through hole, said solid-state image sensing device being secured to said package via an adhesive.
2. A solid-state image apparatus comprising:
  - a package comprising a main body having a through hole therein, said main body having a top surface and a bottom surface, said package further comprising a ledge formed on said main body so as to extend inwardly toward the center of said through hole, said ledge comprising an upper surface and a lower surface;
  - a lead frame comprising inner leads and outer leads, said lead frame being sealed in said package such that said inner leads extend inwardly from said main body so as to be adjacent said lower surface of said ledge; and
  - a solid-state image sensing device having an upper surface and a lower surface and a plurality of electrode pads disposed on said upper surface, each of said plurality of electrode pads coupled to one of said inner leads;
 said solid-state image sensing device being secured to said main body of said package via an adhesive.
3. The solid-state image sensing apparatus of claim 2, wherein each of the electrode pads is connected to the inner lead via a bump.
4. The solid-state image sensing apparatus of claim 2, wherein each of the electrode pads is connected to the inner lead via an anisotropic conductor having only vertical conductivity.
5. The solid-state image sensing apparatus of claim 2, wherein a tip of the inner lead to which the electrode pad is connected extends beyond said ledge.
6. A solid-state image sensing apparatus comprising:
  - a package having a through hole therein, openings on both end faces thereof, and different opening areas of said openings,
  - a lead frame comprising inner leads and outer leads, said lead frame being sealed in said package,
  - a substrate on which a solid-state image sensing device and a peripheral circuit chip are mounted being inserted into the package from a wider opening thereof, and

- an electrode pad of said substrate being connected to said inner lead exposed from around a smaller opening of said package,
  - said substrate being secured to said package via an adhesive.
7. A solid-state image sensing apparatus comprising:
    - a package having a through hole therein, openings on both end faces thereof, and different opening areas of said openings,
    - a lead frame comprising inner leads and outer leads, said lead frame being sealed in said package,
    - a semiconductor substrate having a solid-state image sensing device and a peripheral circuit chip disposed on an upper surface thereof, said semiconductor substrate being inserted into a plastic package via the larger of two openings formed in said package, and
    - an electrode pad of said semiconductor substrate being connected to the inner lead exposed from around the smaller opening of said package,
 said semiconductor substrate being secured to said package via an adhesive.
  8. The solid state image sensing apparatus of claim 6 or claim 7, wherein a shading film covers an entire upper surface of said substrate except an upper surface of the solid-state image sensing device.
  9. The solid-state image sensing apparatus of claim 6 or claim 7, wherein an electrode pad formed on the substrate is connected to the inner lead via a bump.
  10. The solid-state image sensing apparatus of claim 6 or claim 7, wherein an electrode pad formed on the substrate is connected to the inner lead via an anisotropic conductor which has only vertical conductivity.
  11. The solid-state image sensing apparatus of claim 6 or claim 7, wherein an electrode pad formed on the substrate is connected to the inner lead at an outer portion of said lead, said outer portion of said lead extending into the openings of the package.
  12. A solid-state image sensing apparatus comprising:
    - a package having a through hole therein, openings on both end faces thereof, and different opening areas of said openings,
    - a lead frame comprising inner leads and outer leads, said lead frame being sealed in said package, and
    - a solid-state image sensing device and a peripheral circuit chip both mounted in said package, said solid-state image sensing device being connected to a first inner lead exposed beneath a first step surface formed in said package, said solid-state image sensing device being secured to said package via an adhesive, and said peripheral circuit chip being connected to a second inner lead exposed beneath a second step surface formed in said package, said peripheral circuit chip being secured to said package via an adhesive.
  13. A manufacturing method of a solid-state image sensing apparatus comprising a package having a through hole therein, a lead frame comprising inner leads and outer leads, said lead frame being sealed in said package, and a solid-state image sensing device mounted in said package, said manufacturing method comprising the steps of:
    - inserting said solid-state image sensing device into said through hole,
    - connecting an electrode pad of the solid-state image sensing device inserted in the through hole to the inner lead via a bump or an anisotropic conductor having only vertical conductivity, while simultaneously adjust-

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ing the optical positioning of said solid-state image sensing device, and

securing said solid-state image sensing device to the package with an adhesive.

**14.** A manufacturing method of a solid-state image sensing apparatus comprising a package having a through hole therein, a lead frame comprising inner leads and outer leads, said lead frame being sealed in said package, and a solid-state image sensing device as well as a peripheral circuit chip mounted in said package, said manufacturing method comprising the steps of:

forming said solid-state image sensing device and a group of wirings on a semiconductor substrate,

mounting said peripheral circuit chip on the solid-state image sensing device to connect with said group of said semiconductor surface,

inserting said semiconductor substrate into the through hole,

connecting an electrode pad disposed on the semiconductor substrate to the inner lead via a bump or an anisotropic conductor having only vertical conductivity, while simultaneously adjusting the optical positioning of said solid-state image sensing device, and

securing the semiconductor substrate on which the solid-state image sensing device and the peripheral circuit chip are mounted to the package via an adhesive.

**15.** A manufacturing method of a solid-state image sensing apparatus comprising a package having a through hole therein, a lead frame comprising inner leads and outer leads, said lead frame being sealed in said package, and a solid-state image sensing device as well as a peripheral circuit chip mounted in said package, said manufacturing method comprising steps of:

mounting said solid-state image sensing device and said peripheral circuit chip on a substrate where a group of wirings is disposed in order to connect the solid-state image sensing device and the peripheral circuit chip to the group of wirings,

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inserting the semiconductor substrate into the through hole,

connecting an electrode pad disposed on a periphery of the substrate to the inner lead via a bump or an anisotropic conductor having only vertical conductivity, while simultaneously adjusting the optical positioning of the solid-state image sensing device, and

securing the semiconductor substrate on which said solid-state image sensing device and said peripheral circuit chip are mounted to the package via an adhesive.

**16.** A manufacturing method of a solid-state image sensing apparatus comprising a package having a through hole therein, a lead frame comprising inner leads and outer leads, said lead frame being sealed in the package, and a solid-state image sensing device as well as a peripheral circuit chip mounted in said package, said manufacturing method comprising steps of:

inserting said solid-state image sensing device into the through hole,

connecting an electrode pad of the solid-state image sensing device to a first inner lead via a bump or an anisotropic conductor having only vertical conductivity, while simultaneously adjusting the optical positioning of the solid-state image sensing device, said first inner lead being disposed beneath a first step surface formed in said package,

securing the solid-state image sensing device to the package via an adhesive,

inserting the peripheral circuit chip into the through hole, connecting an electrode pad of the peripheral circuit chip to a second inner lead via a bump or an anisotropic conductor having only vertical conductivity, to complete an electrical connection, said second inner lead being disposed beneath a second step surface formed in said package, and

securing the peripheral circuit chip to the package via an adhesive.

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UNITED STATES PATENT AND TRADEMARK OFFICE  
**CERTIFICATE OF CORRECTION**

PATENT NO. : 5,952,714  
DATED : September 14, 1999  
INVENTOR(S) : Sano et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

**On the cover page:**

At the end of the "FOREIGN PATENT DOCUMENTS" section, insert:

--63-274162 11/88 Japan--.

Signed and Sealed this  
Fifth Day of September, 2000

Attest:



Q. TODD DICKINSON

Attesting Officer

Director of Patents and Trademarks